

ABSTRACT

Semiconductor wafers are cleaned by placing the semiconductor wafers in a processing vessel, forming a pure water
5 film on the surfaces of the wafers, forming an ozonic water film
by dissolving ozone gas in the pure water film, and removing resist
films formed on the wafers by the agency of the ozonic water film.
The pure water film is formed by condensing steam on the surfaces
of the wafers. The resist films formed on the surfaces of the
10 wafers can be removed by also using hydroxyl radicals produced
by interaction between steam and ozone gas supplied into the
processing vessel. Thus, the resist films can be removed highly
effectively.